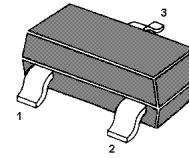


MMBTSC2714

NPN Silicon Epitaxial Planar Transistor

for high frequency amplifier at FM,RF,MIX, and IF amplifier applications.

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.



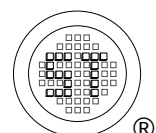
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Base Current	I_B	4	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_{amb}=25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$ Current Gain Group R O Y	h_{FE}	40	-	80	-
	h_{FE}	70	-	140	-
	h_{FE}	100	-	200	-
Collector Base Cutoff Current at $V_{CB} = 18\text{ V}$	I_{CBO}	-	-	500	nA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	-	500	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	40	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	30	-	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	4	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V
Transition Frequency at $V_{CE} = 6\text{ V}$, $I_C = 1\text{ mA}$	f_T	-	550	-	MHz
Reverse Transfer Capacitance at $V_{CB} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{re}	-	0.7	-	pF



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